

# NTD80N02 Datasheet



https://www.DiGi-Electronics.com

DiGi Electronics Part Number NTD80N02-DG

Manufacturer onsemi

Manufacturer Product Number NTD80N02

Description MOSFET N-CH 24V 80A DPAK

Detailed Description N-Channel 24 V 80A (Tc) 75W (Tc) Surface Mount D

PAK



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# **Purchase and inquiry**

| Manufacturer Product Number:            | Manufacturer:                           |
|---|---|
| NTD80N02                                | onsemi                                  |
| Series:                                 | Product Status:                         |
|   | Obsolete                                |
| FET Type:                               | Technology:                             |
| N-Channel                               | MOSFET (Metal Oxide)                    |
| Drain to Source Voltage (Vdss):         | Current - Continuous Drain (Id) @ 25°C: |
| 24 V                                    | 80A (Tc)                                |
| Drive Voltage (Max Rds On, Min Rds On): | Rds On (Max) @ ld, Vgs:                 |
| 4.5V, 10V                               | 5.8mOhm @ 80A, 10V                      |
| Vgs(th) (Max) @ ld:                     | Gate Charge (Qg) (Max) @ Vgs:           |
| 3V @ 250μA                              | 42 nC @ 4.5 V                           |
| Vgs (Max):                              | Input Capacitance (Ciss) (Max) @ Vds:   |
| ±20V                                    | 2600 pF @ 20 V                          |
| FET Feature:                            | Power Dissipation (Max):                |
|   | 75W (Tc)                                |
| Operating Temperature:                  | Mounting Type:                          |
| -55°C ~ 150°C (TJ)                      | Surface Mount                           |
| Supplier Device Package:                | Package / Case:                         |
| DPAK                                    | TO-252-3, DPAK (2 Leads + Tab), SC-63   |
| Base Product Number:                    |   |
| NTD80                                   |   |

# **Environmental & Export classification**

8541.29.0095

| RoHS Status:       | Moisture Sensitivity Level (MSL): |
|--------------------|-----------------------------------|
| RoHS non-compliant | 1 (Unlimited)                     |
| REACH Status:      | ECCN:                             |
| REACH Unaffected   | EAR99                             |
| HTSUS:             |                                   |

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### **Power MOSFET**

# 24 V, 80 A, N-Channel DPAK

Designed for low voltage, high speed switching applications in power supplies, converters and power motor controls and bridge circuits.

#### **Features**

• These Devices are Pb-Free and are RoHS Compliant

#### **Typical Applications**

- Power Supplies
- Converters
- Power Motor Controls
- Bridge Circuits

#### MAXIMUM RATINGS (T<sub>J</sub> = 25°C unless otherwise noted)

| Rating   | Symbol  | Value             | Unit  |
|--|---|-------------------|-------|
| Drain-to-Source Voltage  | $V_{DSS}$   | 24                | Vdc   |
| Gate-to-Source Voltage - Continuous  | $V_{GS}$  | ±20               | Vdc   |
| Drain Current – Continuous @ $T_C$ = 25°C – Single Pulse ( $t_p$ = 10 $\mu$ s)   | I <sub>D</sub><br>I <sub>DM</sub>                                       | 80*<br>200        | Adc   |
| Total Power Dissipation @ T <sub>C</sub> = 25°C  | $P_{D}$   | 75                | Watts |
| Operating and Storage<br>Temperature Range   | T <sub>J</sub> , T <sub>stg</sub>                                       | -55 to<br>150     | °C    |
| Single Pulse Drain-to-Source Avalanche<br>Energy – Starting $T_J$ = 25°C<br>( $V_{DD}$ = 24 Vdc, $V_{GS}$ = 10 Vdc,<br>$I_L$ = 17 Apk, $L$ = 5.0 mH, $R_G$ = 25 $\Omega$ ) | E <sub>AS</sub>   | 733               | mJ    |
| Thermal Resistance  – Junction-to-Case  – Junction-to-Ambient (Note 1)  – Junction-to-Ambient (Note 2)   | $egin{array}{c} R_{	heta JC} \ R_{	heta JA} \ R_{	heta JA} \end{array}$ | 1.65<br>67<br>120 | °C/W  |
| Maximum Lead Temperature for Soldering Purposes, 1/8" from case for 10 seconds   | TL  | 260               | °C    |

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

- When surface mounted to an FR4 board using 1" pad size, (Cu Area 1.127 in<sup>2</sup>).
- When surface mounted to an FR4 board using the minimum recommended pad size, (Cu Area 0.412 in<sup>2</sup>).

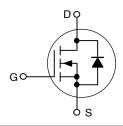


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| V <sub>(BR)DSS</sub> | R <sub>DS(on)</sub> TYP | I <sub>D</sub> MAX |
|----------------------|-------------------------|--------------------|
| 24 V                 | 5.0 mΩ                  | 80 A               |

#### N-Channel



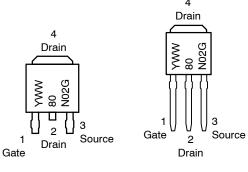






CASE 369AA CASE 369C CASE 369D
DPAK DPAK DPAK
(Surface Mount) (Surface Mount) (Straight Lead)
STYLE 2 STYLE 2 STYLE 2

# MARKING DIAGRAMS & PIN ASSIGNMENTS



80N02 = Device Code Y = Year WW = Work Week G = Pb-Free Package

#### **ORDERING INFORMATION**

See detailed ordering and shipping information in the package dimensions section on page 5 of this data sheet.

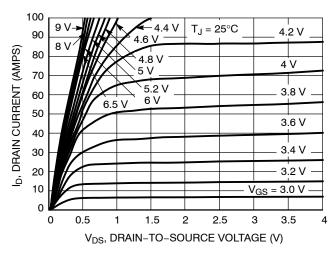
<sup>\*</sup>Chip current capability limited by package.

### **ELECTRICAL CHARACTERISTICS** ( $T_J = 25^{\circ}C$ unless otherwise noted)

| Char  | Symbol   | Min                 | Тур                      | Max                      | Unit          |      |
|---|--|---------------------|--------------------------|--------------------------|---------------|------|
| OFF CHARACTERISTICS   |  |                     |                          |                          |               |      |
| Drain-to-Source Breakdown Voltage (V <sub>GS</sub> = 0 Vdc, I <sub>D</sub> = 250 µAdc) Positive Temperature Coefficient   | V <sub>(BR)DSS</sub>                               | 24<br>-             | 27<br>25                 | <u>-</u>                 | Vdc<br>mV/°C  |      |
| Zero Gate Voltage Drain Current $(V_{GS} = 0 \text{ Vdc}, V_{DS} = 24 \text{ Vdc})$ $(V_{GS} = 0 \text{ Vdc}, V_{DS} = 24 \text{ Vdc}, T_J = 24 \text{ Vdc})$   | = 125°C)   | I <sub>DSS</sub>    | -<br>-                   | -<br>-                   | 1.0<br>10     | μAdc |
| Gate-Body Leakage Current (V <sub>GS</sub> :  | = ±20 Vdc, V <sub>DS</sub> = 0 Vdc)                | I <sub>GSS</sub>    | -                        | _                        | ±100          | nAdc |
| ON CHARACTERISTICS (Note 3)   |  |                     |                          |                          |               |      |
| Gate Threshold Voltage (Note 3) $(V_{DS} = V_{GS}, I_D = 250  \mu \text{Adc})$ Negative Threshold Temperature C   | V <sub>GS(th)</sub>                                | 1.0                 | 1.9<br>-3.8              | 3.0                      | Vdc<br>mV/°C  |      |
| $ \begin{array}{c} {\rm Static\ Drain-to-Source\ On-Resista} \\ ({\rm V_{GS}}=10\ {\rm Vdc},\ {\rm I_{D}}=80\ {\rm Adc}) \\ ({\rm V_{GS}}=4.5\ {\rm Vdc},\ {\rm I_{D}}=40\ {\rm Adc}) \\ ({\rm V_{GS}}=10\ {\rm Vdc},\ {\rm I_{D}}=20\ {\rm Adc}) \\ ({\rm V_{GS}}=4.5\ {\rm Vdc},\ {\rm I_{D}}=20\ {\rm Adc}) \\ \end{array} $ | R <sub>DS(on)</sub>                                | -<br>-<br>-         | 5.0<br>7.5<br>5.0<br>7.5 | 5.8<br>9.0<br>5.8<br>9.0 | mΩ            |      |
| Forward Transconductance (V <sub>DS</sub> =   | 15 Vdc, I <sub>D</sub> = 10 Adc) (Note 3)          | 9FS                 | _                        | 20                       | -             | Mhos |
| DYNAMIC CHARACTERISTICS   |  |                     |                          |                          |               |      |
| Input Capacitance   | (V <sub>DS</sub> = 20 Vdc,                         | C <sub>iss</sub>    | -                        | 2250                     | 2600          | pF   |
| Output Capacitance  | $V_{GS} = 0 V$                                     | C <sub>oss</sub>    | -                        | 900                      | 1100          |      |
| Transfer Capacitance  | f = 1.0 MHz)                                       | C <sub>rss</sub>    | -                        | 400                      | 525           |      |
| SWITCHING CHARACTERISTICS (N  | lote 4)  |                     |                          |                          |               |      |
| Turn-On Delay Time  | (V <sub>GS</sub> = 4.5 Vdc,                        | t <sub>d(on)</sub>  | -                        | 17                       | 30            | ns   |
| Rise Time   | $V_{DD} = 20 \text{ Vdc},$                         | t <sub>r</sub>      | _                        | 67                       | 125           |      |
| Turn-Off Delay Time   | $I_{D} = 20 \text{ Adc},$                          | t <sub>d(off)</sub> | -                        | 28                       | 45            |      |
| Fall Time   | $R_G = 2.5 \Omega$ )                               | t <sub>f</sub>      | _                        | 40                       | 75            |      |
| Gate Charge   | (V <sub>GS</sub> = 4.5 Vdc,                        | Q <sub>T</sub>      | -                        | 30                       | 42            | nC   |
|   | $I_D = 20 \text{ Adc},$                            | Q1                  | _                        | 7.0                      | 12            |      |
|   | V <sub>DS</sub> = 20 Vdc) (Note 3)                 | Q2                  | -                        | 18                       | 28            |      |
| SOURCE-DRAIN DIODE CHARACT  | ERISTICS   |                     |                          |                          |               |      |
| Forward On–Voltage  |  | V <sub>SD</sub>     | -<br>-<br>-              | 0.92<br>1.05<br>0.70     | 1.2<br>-<br>- | Vdc  |
| Reverse Recovery Time   | (I <sub>S</sub> = 20 Adc, V <sub>GS</sub> = 0 Vdc, | t <sub>rr</sub>     | _                        | 38                       | 52            | ns   |
|   |  | t <sub>a</sub>      | _                        | 20                       | _             | 1    |
|   | $dI_S/dt = 100 A/\mu s)$ (Note 3)                  | t <sub>b</sub>      | _                        | 18                       | -             | ]    |
| Reverse Recovery Stored Charge  | Q <sub>rr</sub>                                    | _                   | 0.038                    | -                        | μС            |      |

Pulse Test: Pulse Width ≤ 300 μs, Duty Cycle ≤ 2%.
 Switching characteristics are independent of operating junction temperatures.

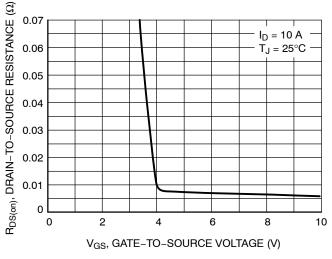
#### **TYPICAL CHARACTERISTICS**



160 150  $V_{DS} \ge 24 \text{ V}$ 140 130 120 DRAIN CURRENT (AMPS) 110 100 80 70 T<sub>J</sub> = 25°C 60 50 40  $T_J = 125^{\circ}C$ 30 20  $T_J = -55^{\circ}C$ 10 ڡٞ 2 V<sub>GS</sub>, GATE-TO-SOURCE VOLTAGE (V)

Figure 1. On-Region Characteristics

Figure 2. Transfer Characteristics



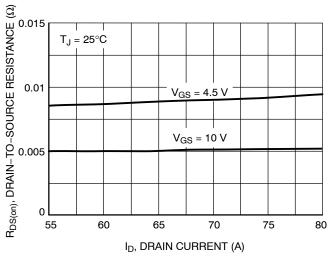
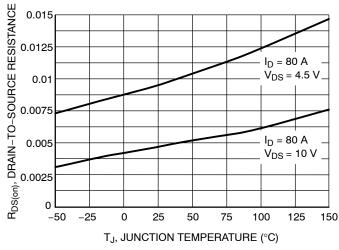


Figure 3. On-Resistance versus Gate-To-Source Voltage

Figure 4. On-Resistance versus Drain Current and Gate Voltage



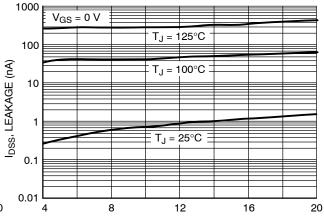


Figure 5. On–Resistance Variation with Temperature

Figure 6. Drain-To-Source Leakage Current versus Voltage

V<sub>DS</sub>, DRAIN-TO-SOURCE VOLTAGE (V)

#### **TYPICAL CHARACTERISTICS**

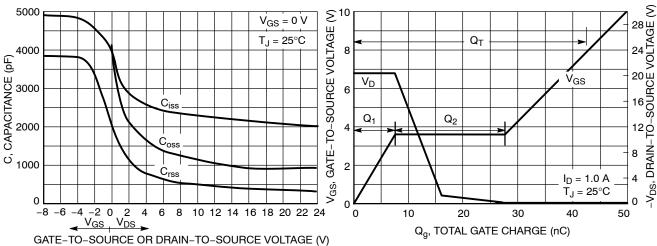


Figure 7. Capacitance Variation

Figure 8. Gate-to-Source and Drain-to-Source Voltage versus Total Charge

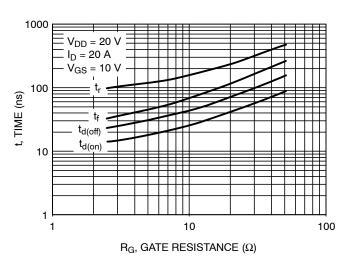
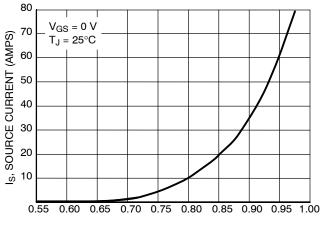


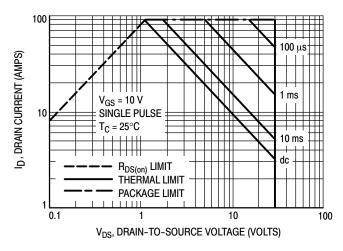
Figure 9. Resistive Switching Time Variation versus Gate Resistance



V<sub>SD</sub>, SOURCE-TO-DRAIN VOLTAGE (V)

Figure 10. Diode Forward Voltage versus Current

#### **TYPICAL CHARACTERISTICS**



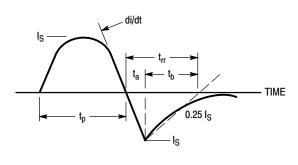


Figure 11. Maximum Rated Forward Biased Safe Operating Area

Figure 12. Diode Reverse Recovery Waveform

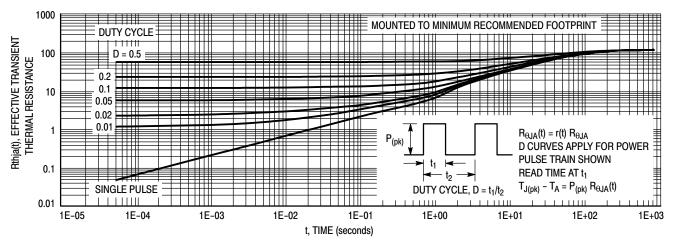


Figure 13. Thermal Response - Various Duty Cycles

#### **ORDERING INFORMATION**

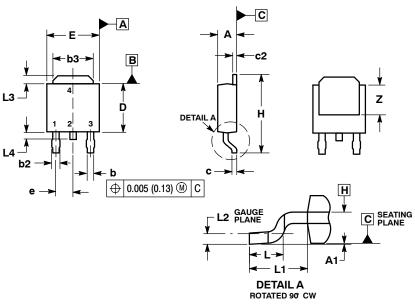
| Order Number | Package                           | Shipping <sup>†</sup> |
|--------------|-----------------------------------|-----------------------|
| NTD80N02T4G  | DPAK-3<br>(Pb-Free)               | 2500 / Tape & Reel    |
| NTD80N02-1G  | DPAK-3 Straight Lead<br>(Pb-Free) | 75 Units / Rail       |

<sup>†</sup>For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

#### PACKAGE DIMENSIONS

### **DPAK (SINGLE GAUGE)**

CASE 369AA-01 **ISSUE B** 



- NOTES:

  1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
  2. CONTROLLING DIMENSION: INCHES.
  3. THERMAL PAD CONTOUR OPTIONAL WITHIN DIMENSIONS b3, L3 and Z.
  4. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR BURRS. MOLD FLASH, PROTRUSIONS, OR GATE BURRS SHALL NOT EXCEED 0 0006 INCHES PER SIDE
- NOT EXCEED 0.006 INCHES PER SIDE.

  5. DIMENSIONS D AND E ARE DETERMINED AT THE OUTERMOST EXTREMES OF THE PLASTIC BODY.

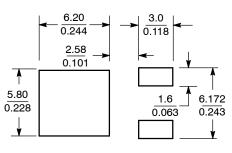
  6. DATUMS A AND B ARE DETERMINED AT DATUM

|     | INCHES    |           | MILLIMETERS |       |
|-----|-----------|-----------|-------------|-------|
| DIM | MIN       | MAX       | MIN         | MAX   |
| Α   | 0.086     | 0.094     | 2.18        | 2.38  |
| A1  | 0.000     | 0.005     | 0.00        | 0.13  |
| b   | 0.025     | 0.035     | 0.63        | 0.89  |
| b2  | 0.030     | 0.045     | 0.76        | 1.14  |
| b3  | 0.180     | 0.215     | 4.57        | 5.46  |
| c   | 0.018     | 0.024     | 0.46        | 0.61  |
| c2  | 0.018     | 0.024     | 0.46        | 0.61  |
| D   | 0.235     | 0.245     | 5.97        | 6.22  |
| Е   | 0.250     | 0.265     | 6.35        | 6.73  |
| e   | 0.090 BSC |           | 2.29        | BSC   |
| Η   | 0.370     | 0.410     | 9.40        | 10.41 |
| L   | 0.055     | 0.070     | 1.40        | 1.78  |
| L1  | 0.108     | 0.108 REF |             | REF   |
| L2  | 0.020     | BSC       | 0.51 BSC    |       |
| L3  | 0.035     | 0.050     | 0.89        | 1.27  |
| L4  |           | 0.040     |             | 1.01  |
| Z   | 0.155     |           | 3.93        |       |

STYLE 2: PIN 1. GATE 2. DRAIN 3. SOURCE

4. DRAIN

#### **SOLDERING FOOTPRINT\***



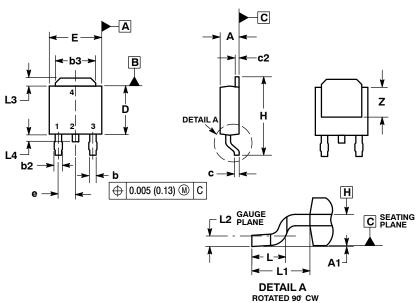
 $\left(\frac{\text{mm}}{\text{inches}}\right)$ SCALE 3:1

<sup>\*</sup>For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

#### PACKAGE DIMENSIONS

### **DPAK (SINGLE GAUGE)**

CASE 369C-01 ISSUE D



#### NOTES:

- NOTES:

  1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.

  2. CONTROLLING DIMENSION: INCHES.

  3. THERMAL PAD CONTOUR OPTIONAL WITHIN DIMENSIONS b3, L3 and Z.

  4. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR BURRS. MOLD FLASH, PROTRUSIONS, OR GATE BURRS SHALL NOT EXCEED 0.006 INCHES PER SIDE.

  5. DIMENSIONS D AND E ARE DETERMINED AT THE OUTERMOST EXTREMES OF THE PLASTIC BODY.

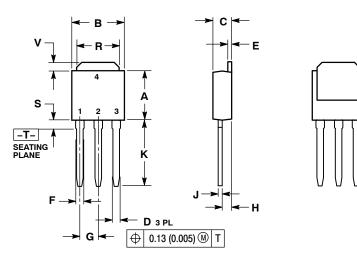
  6. DATUMS A AND B ARE DETERMINED AT DATUM PLANE H.

|     | INC       | HES   | MILLIN   | IETERS |
|-----|-----------|-------|----------|--------|
| DIM | MIN       | MAX   | MIN      | MAX    |
| Α   | 0.086     | 0.094 | 2.18     | 2.38   |
| A1  | 0.000     | 0.005 | 0.00     | 0.13   |
| b   | 0.025     | 0.035 | 0.63     | 0.89   |
| b2  | 0.030     | 0.045 | 0.76     | 1.14   |
| b3  | 0.180     | 0.215 | 4.57     | 5.46   |
| С   | 0.018     | 0.024 | 0.46     | 0.61   |
| c2  | 0.018     | 0.024 | 0.46     | 0.61   |
| D   | 0.235     | 0.245 | 5.97     | 6.22   |
| Е   | 0.250     | 0.265 | 6.35     | 6.73   |
| е   | 0.090 BSC |       | 2.29     | BSC    |
| Н   | 0.370     | 0.410 | 9.40     | 10.41  |
| L   | 0.055     | 0.070 | 1.40     | 1.78   |
| L1  | 0.108 REF |       | 2.74 REF |        |
| L2  | 0.020     | BSC   | 0.51 BSC |        |
| L3  | 0.035     | 0.050 | 0.89     | 1.27   |
| L4  |           | 0.040 |          | 1.01   |
| Z   | 0.155     |       | 3.93     |        |

- STYLE 2: PIN 1. GATE 2. DRAIN 3. SOURCE 4. DRAIN

#### PACKAGE DIMENSIONS

#### **DPAK** CASE 369D-01 **ISSUE B**



#### NOTES:

- DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982. 2. CONTROLLING DIMENSION: INCH.

|     | INCHES    |       | MILLIN | IETERS |
|-----|-----------|-------|--------|--------|
| DIM | MIN       | MAX   | MIN    | MAX    |
| Α   | 0.235     | 0.245 | 5.97   | 6.35   |
| В   | 0.250     | 0.265 | 6.35   | 6.73   |
| С   | 0.086     | 0.094 | 2.19   | 2.38   |
| D   | 0.027     | 0.035 | 0.69   | 0.88   |
| E   | 0.018     | 0.023 | 0.46   | 0.58   |
| F   | 0.037     | 0.045 | 0.94   | 1.14   |
| G   | 0.090 BSC |       | 2.29   | BSC    |
| Н   | 0.034     | 0.040 | 0.87   | 1.01   |
| J   | 0.018     | 0.023 | 0.46   | 0.58   |
| K   | 0.350     | 0.380 | 8.89   | 9.65   |
| R   | 0.180     | 0.215 | 4.45   | 5.45   |
| S   | 0.025     | 0.040 | 0.63   | 1.01   |
| V   | 0.035     | 0.050 | 0.89   | 1.27   |
| Z   | 0.155     |       | 3.93   |        |

STYLE 2: PIN 1. GATE

- 2 DRAIN
- SOURCE
- DRAIN

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